March 1996

FAIRCHILD

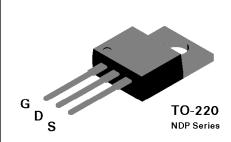
NDP6060 / NDB6060 N-Channel Enhancement Mode Field Effect Transistor

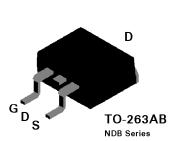
General Description

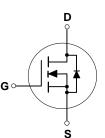
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as automotive, DC/DC converters, PWM motor controls, and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

- 48A, 60V. $R_{DS(ON)} = 0.025\Omega @ V_{GS} = 10V.$
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- 175°C maximum junction temperature rating.
- High density cell design for extremely low R_{DS(ON)}.
- TO-220 and TO-263 (D²PAK) package for both through hole and surface mount applications.







Absolute Maximum Ratings T_c = 25°C unless otherwise noted

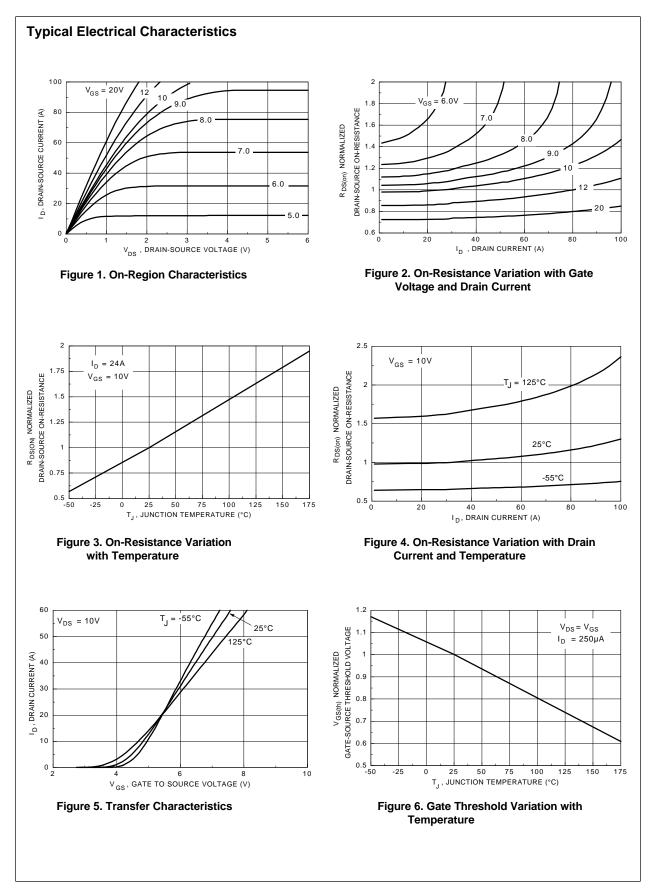
Symbol	Parameter	NDP6060	NDB6060	Units
V _{DSS}	Drain-Source Voltage	60		
V_{DGR}	Drain-Gate Voltage ($R_{GS} \le 1 M\Omega$) 60			V
V _{GSS}	Gate-Source Voltage - Continuous	± 20		V
	- Nonrepetitive ($t_p < 50 \ \mu s$) ± 40			
I _D	Drain Current - Continuous T _c =25°C	48		А
	- Continuous T _c =100°C	32		
	- Pulsed	144		
P _D	Total Power Dissipation @ $T_c = 25^{\circ}C$	100		
	Derate above 25°C	0.67		
T_,T _{stg}	Operating and Storage Temperature Range	-65 to 175		
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	275		°C

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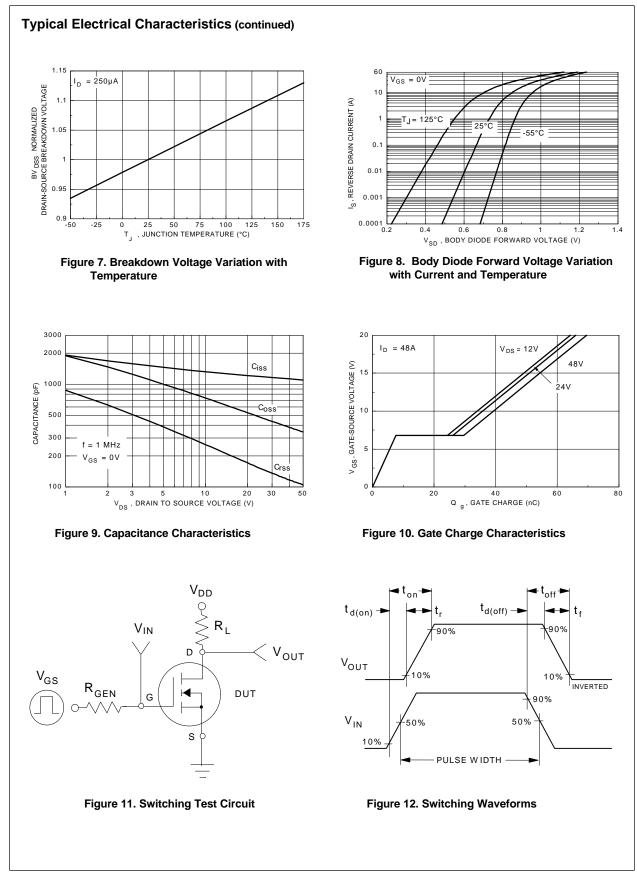
Symbol	Parameter	Conditions		Min	Тур	Max	Units
DRAIN-SO	DURCE AVALANCHE RATINGS (Note 1)	•					
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 25 \text{ V}, \text{ I}_{D} = 48 \text{ A}$				200	mJ
I _{AR}	Maximum Drain-Source Avalanche Cur	rent				48	Α
OFF CHA	RACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = 250 \mu A$		60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 60 V, V _{GS} = 0 V				250	μA
			T _J = 125°C			1	mA
I _{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$				-100	nA
ON CHAF	RACTERISTICS (Note 1)	·					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		2	2.9	4	V
			T _J = 125°C	1.4	2.3	3.6	
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 24 A			0.02	0.025	Ω
			T _J = 125°C		0.032	0.04	
l _{D(on)}	On-State Drain Current	$V_{GS} = 10 \text{ V}, \text{ V}_{DS} = 10 \text{ V}$		48			Α
9 _{FS}	Forward Transconductance	$V_{\rm DS} = 10 \text{ V}, I_{\rm D} = 24 \text{ A}$		10	19		S
DYNAMIC	CHARACTERISTICS						
C _{iss}	Input Capacitance	$V_{\rm DS} = 25 \text{ V}, \ V_{\rm GS} = 0 \text{ V},$			1190	1800	pF
C _{oss}	Output Capacitance	f = 1.0 MHz			475	800	pF
C _{rss}	Reverse Transfer Capacitance	1			150	400	pF
	NG CHARACTERISTICS (Note 1)	1		1			
t _{D(on)}	Turn - On Delay Time	$V_{DD} = 30 \text{ V}, \ \text{I}_{D} = 48 \text{ A},$ $V_{GS} = 10 \text{ V}, \ \text{R}_{GEN} = 7.5 \ \Omega$			10	20	nS
ţ,	Turn - On Rise Time				145	300	nS
t _{D(off)}	Turn - Off Delay Time				28	60	nS
t _f	Turn - Off Fall Time				77	150	nS
<u>4</u> Q_	Total Gate Charge	V ₁₀₀ = 48 V.			39	70	nC
Q _{gs}	Gate-Source Charge	$V_{DS} = 48 V,$ $I_{D} = 48 A, V_{GS} = 10V$			7.6		nC
<u>∽_{gs}</u> Q _{gd}	Gate-Drain Charge	-			22		nC

Symbol	Parameter	Conditions		Min	Тур	Max	Units
DRAIN-SO	OURCE DIODE CHARACTERISTICS						
s	Maximum Continuos Drain-Source Diode Forward Current				48	Α	
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current					144	А
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_{S} = 24 A (Note 1)$			0.9	1.3	V
			T _J = 125°C		0.8	1.2	
'n	Reverse Recovery Time	$V_{GS} = 0 V, I_F = 48 A,$		35	87	140	ns
l _m	Reverse Recovery Current	— dl _⊧ /dt = 100 A/µs		2	3.6	8	А
THERMA	L CHARACTERISTICS						
R _{ØJC}	Thermal Resistance, Junction-to-Case					1.5	°C/W
R _{ØJA}	Thermal Resistance, Junction-to-Ambient					62.5	°C/W

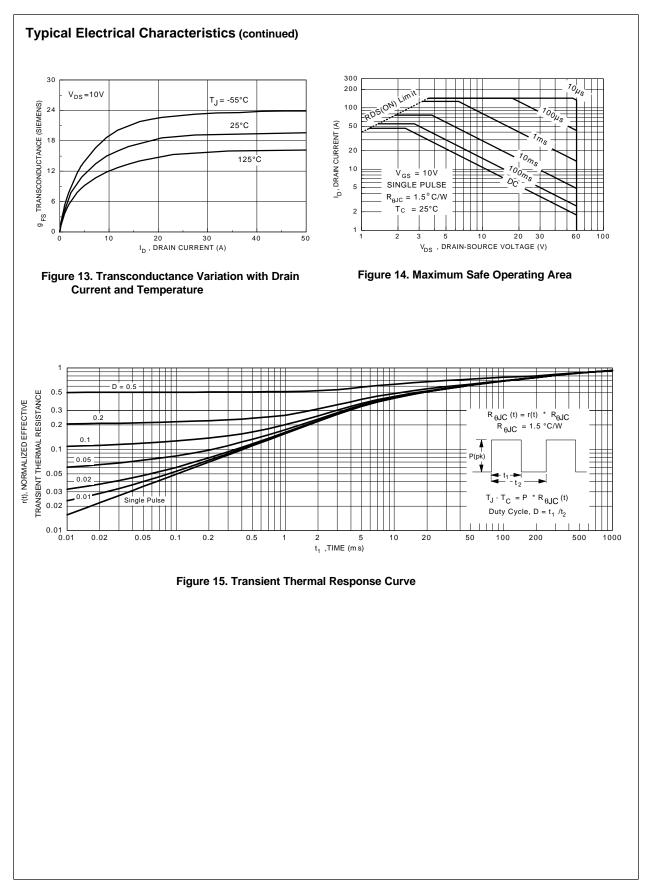
Note: 1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.



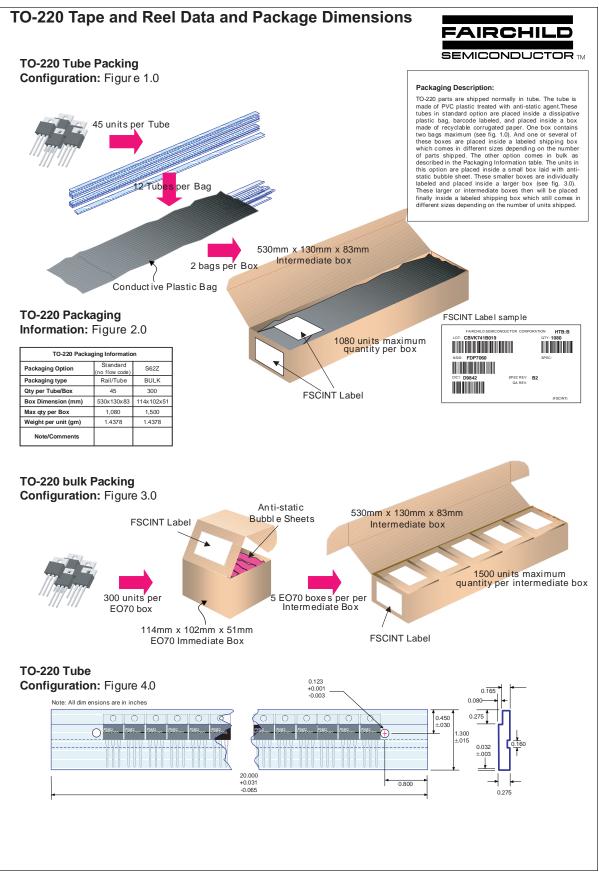
NDP6060 Rev. B1 / NDB6060 Rev. C



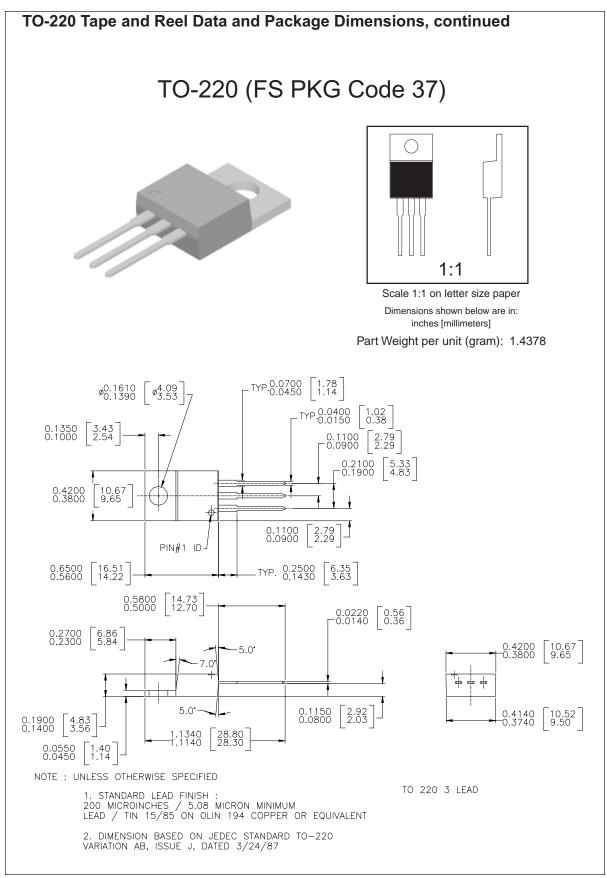
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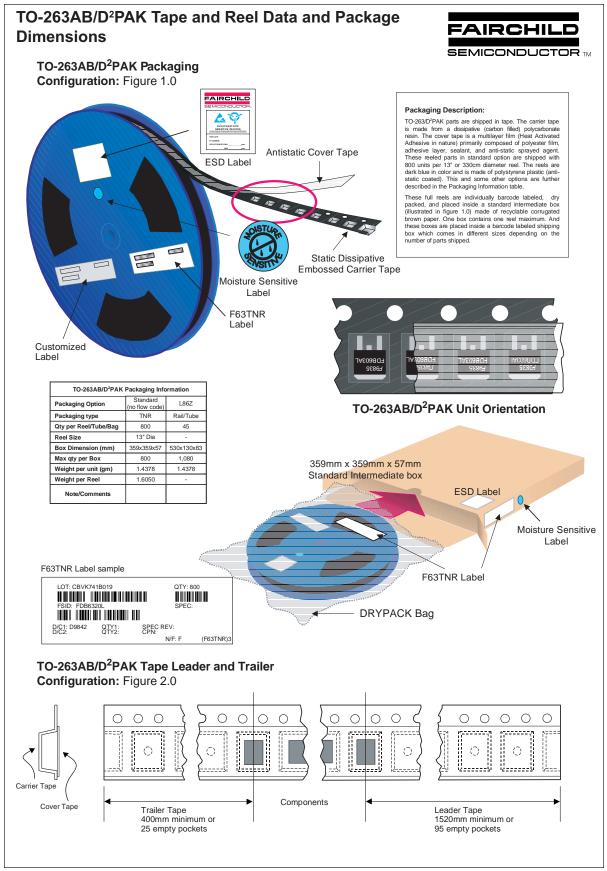
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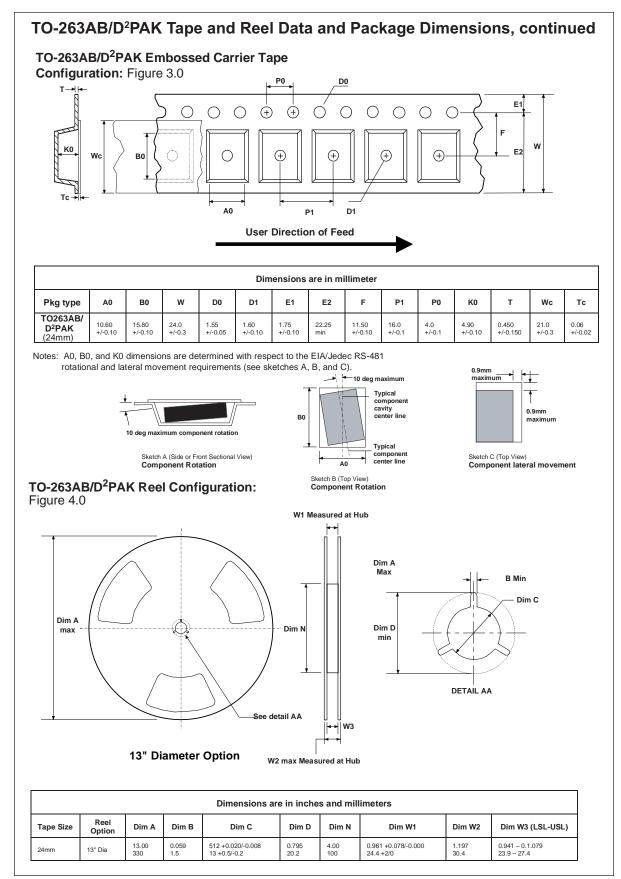
August 1999, Rev. B

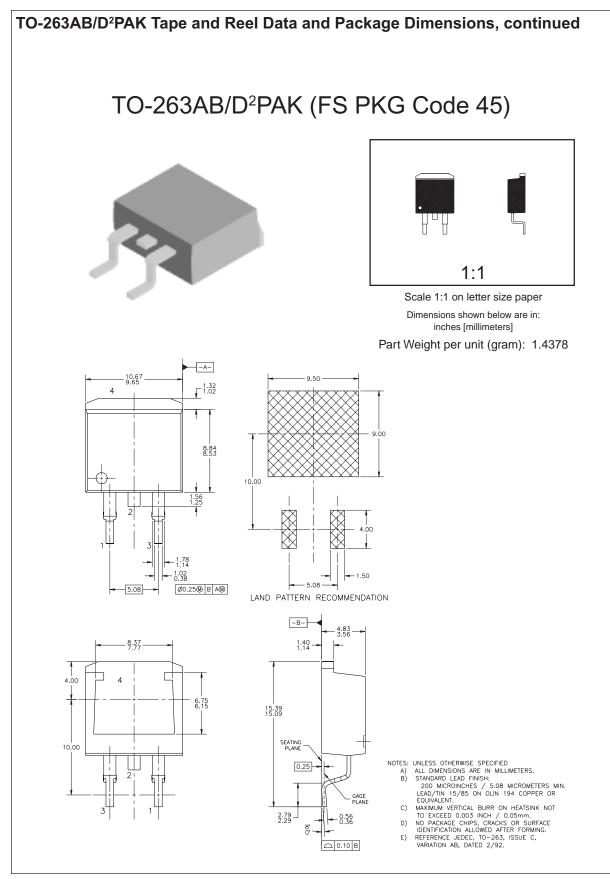


September 1998, Rev. A



September 1999, Rev. B





August 1998, Rev. A

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